

# Sayeef Salahuddin

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

151 papers	8,593 citations	46 h-index	90 g-index
174 ext. papers	10,732 ext. citations	8.1 avg, IF	6.54 L-index

#	Paper	IF	Citations
151	Use of negative capacitance to provide voltage amplification for low power nanoscale devices. <i>Nano Letters</i> , <b>2008</b> , 8, 405-10	11.5	1257
150	Memory leads the way to better computing. <i>Nature Nanotechnology</i> , <b>2015</b> , 10, 191-4	28.7	497
149	Deterministic switching of ferromagnetism at room temperature using an electric field. <i>Nature</i> , <b>2014</b> , 516, 370-3	50.4	449
148	Negative capacitance in a ferroelectric capacitor. <i>Nature Materials</i> , <b>2015</b> , 14, 182-6	27	438
147	Room-temperature antiferromagnetic memory resistor. <i>Nature Materials</i> , <b>2014</b> , 13, 367-74	27	435
146	Enhanced ferroelectricity in ultrathin films grown directly on silicon. <i>Nature</i> , <b>2020</b> , 580, 478-482	50.4	232
145	Experimental evidence of ferroelectric negative capacitance in nanoscale heterostructures. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 113501	3.4	210
144	The era of hyper-scaling in electronics. <i>Nature Electronics</i> , <b>2018</b> , 1, 442-450	28.4	190
143	Ferroelectric negative capacitance MOSFET: Capacitance tuning & antiferroelectric operation <b>2011</b> ,		180
142	Sustained Sub-60 mV/decade Switching via the Negative Capacitance Effect in MoS Transistors. <i>Nano Letters</i> , <b>2017</b> , 17, 4801-4806	11.5	179
141	Spin Hall effect clocking of nanomagnetic logic without a magnetic field. <i>Nature Nanotechnology</i> , <b>2014</b> , 9, 59-63	28.7	170
140	Direct Observation of Negative Capacitance in Polycrystalline Ferroelectric HfO <sub>2</sub> . <i>Advanced Functional Materials</i> , <b>2016</b> , 26, 8643-8649	15.6	168
139	Built-in and induced polarization across LaAlO <sub>3</sub> /SrTiO <sub>3</sub> heterojunctions. <i>Nature Physics</i> , <b>2011</b> , 7, 80-86	16.2	167
138	Switching of perpendicularly polarized nanomagnets with spin orbit torque without an external magnetic field by engineering a tilted anisotropy. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2015</b> , 112, 10310-5	11.5	162
137	Negative Capacitance in Short-Channel FinFETs Externally Connected to an Epitaxial Ferroelectric Capacitor. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 111-114	4.4	153
136	Spatially resolved steady-state negative capacitance. <i>Nature</i> , <b>2019</b> , 565, 468-471	50.4	144
135	Transport effects on signal propagation in quantum wires. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 1734-1742	2.9	134

134	Large resistivity modulation in mixed-phase metallic systems. <i>Nature Communications</i> , <b>2015</b> , 6, 5959	17.4	132
133	Sub-60mV-swing negative-capacitance FinFET without hysteresis <b>2015</b> ,		123
132	Analysis and Compact Modeling of Negative Capacitance Transistor with High ON-Current and Negative Output Differential ResistancePart II: Model Validation. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 4986-4992	2.9	109
131	Single crystal functional oxides on silicon. <i>Nature Communications</i> , <b>2016</b> , 7, 10547	17.4	106
130	Room-temperature negative capacitance in a ferroelectric-dielectric superlattice heterostructure. <i>Nano Letters</i> , <b>2014</b> , 14, 5814-9	11.5	105
129	Effects of the Variation of Ferroelectric Properties on Negative Capacitance FET Characteristics. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 2197-2199	2.9	103
128	Improved Subthreshold Swing and Short Channel Effect in FDSOI n-Channel Negative Capacitance Field Effect Transistors. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 300-303	4.4	93
127	Negative Capacitance Behavior in a Leaky Ferroelectric. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 4416-4422	2.9	78
126	Ultrafast magnetization reversal by picosecond electrical pulses. <i>Science Advances</i> , <b>2017</b> , 3, e1603117	14.3	77
125	Gate Recessed Quasi-Normally OFF Al <sub>2</sub> O <sub>3</sub> /AlGa <sub>N</sub> /Ga <sub>N</sub> MIS-HEMT With Low Threshold Voltage Hysteresis Using PEALD Al <sub>N</sub> Interfacial Passivation Layer. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 732-734 <sup>4.4</sup>	4.4	70
124	Can the subthreshold swing in a classical FET be lowered below 60 mV/decade? <b>2008</b> ,		68
123	Heterojunction Vertical Band-to-Band Tunneling Transistors for Steep Subthreshold Swing and High on Current. <i>IEEE Electron Device Letters</i> , <b>2011</b> , 32, 689-691	4.4	65
122	Self-Aligned, Gate Last, FDSOI, Ferroelectric Gate Memory Device With 5.5-nm Hf <sub>0.8</sub> Zr <sub>0.2</sub> O <sub>2</sub> , High Endurance and Breakdown Recovery. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1379-1382	4.4	61
121	Negative Capacitance FET With 1.8-nm-Thick Zr-Doped HfO <sub>2</sub> Oxide. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 993-996	4.4	60
120	Impact of Parasitic Capacitance and Ferroelectric Parameters on Negative Capacitance FinFET Characteristics. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 142-144	4.4	60
119	Negative Capacitance Transistors. <i>Proceedings of the IEEE</i> , <b>2019</b> , 107, 49-62	14.3	59
118	High Speed Epitaxial Perovskite Memory on Flexible Substrates. <i>Advanced Materials</i> , <b>2017</b> , 29, 1605699	24	58
117	Implementing p-bits With Embedded MTJ. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1767-1770	4.4	58

116	Spin-orbit torque switching of ultralarge-thickness ferrimagnetic GdFeCo. <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	55
115	Enabling Energy-Efficient Nonvolatile Computing With Negative Capacitance FET. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 3452-3458	2.9	55
114	Compact models of negative-capacitance FinFETs: Lumped and distributed charge models <b>2016</b> ,		55
113	Analysis and Compact Modeling of Negative Capacitance Transistor with High ON-Current and Negative Output Differential ResistancePart I: Model Description. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 4981-4985	2.9	54
112	Switching Energy of Ferromagnetic Logic Bits. <i>IEEE Nanotechnology Magazine</i> , <b>2009</b> , 8, 505-514	2.6	54
111	Interface Engineering of Domain Structures in BiFeO Thin Films. <i>Nano Letters</i> , <b>2017</b> , 17, 486-493	11.5	52
110	High-frequency performance projections for ballistic carbon-nanotube transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2006</b> , 5, 14-22	2.6	51
109	Ferroelectric negative capacitance domain dynamics. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 184101	2.5	50
108	Engineering Negative Differential Resistance in NCFETs for Analog Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 2033-2039	2.9	49
107	Deterministic Domain Wall Motion Orthogonal To Current Flow Due To Spin Orbit Torque. <i>Scientific Reports</i> , <b>2015</b> , 5, 11823	4.9	49
106	Ferroelectric HfO <sub>2</sub> Memory Transistors With High- $\Gamma$ Interfacial Layer and Write Endurance Exceeding 10 <sup>10</sup> Cycles. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	49
105	Work Function Engineering for Performance Improvement in Leaky Negative Capacitance FETs. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1335-1338	4.4	44
104	Intrinsic speed limit of negative capacitance transistors. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1328-1330.	4.4	42
103	A Spin-Orbit-Torque Memristive Device. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1800782	6.4	37
102	Spin wave generation by surface acoustic waves. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 043904	2.5	36
101	Stabilization of ferroelectric phase in tungsten capped Hf <sub>0.8</sub> Zr <sub>0.2</sub> O <sub>2</sub> . <i>Applied Physics Letters</i> , <b>2017</b> , 111, 022907	3.4	36
100	Proposal for Capacitance Matching in Negative Capacitance Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 463-466	4.4	36
99	Ultrafast magnetic switching of GdFeCo with electronic heat currents. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	34

98	2018,		34
97	Nonvolatile MoS <sub>2</sub> field effect transistors directly gated by single crystalline epitaxial ferroelectric. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 023104	3-4	33
96	Electrical Characteristics of n, p-In <sub>0.53</sub> Ga <sub>0.47</sub> As MOSCAPs With In Situ PEALD-AlN Interfacial Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 2774-2778	2-9	33
95	Local negative permittivity and topological phase transition in polar skyrmions. <i>Nature Materials</i> , <b>2021</b> , 20, 194-201	27	33
94	Role of phonon scattering in graphene nanoribbon transistors: Nonequilibrium Green's function method with real space approach. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 203503	3-4	28
93	Experimental Demonstration of a Ferroelectric HfO <sub>2</sub> -Based Content Addressable Memory Cell. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 240-243	4-4	28
92	Differential voltage amplification from ferroelectric negative capacitance. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 253501	3-4	27
91	Circuit performance analysis of negative capacitance FinFETs <b>2016</b> ,		27
90	Voltage-driven, local, and efficient excitation of nitrogen-vacancy centers in diamond. <i>Science Advances</i> , <b>2018</b> , 4, eaat6574	14-3	25
89	Spin-orbit torque and Nernst effect in Bi-Sb/Co heterostructures. <i>Physical Review B</i> , <b>2019</b> , 99,	3-3	24
88	Designing 0.5 V 5-nm HP and 0.23 V 5-nm LP NC-FinFETs With Improved $\{\}_{\text{OFF}}$ Sensitivity in Presence of Parasitic Capacitance. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 1211-1216	2-9	22
87	Highly Scaled, High Endurance, $\bar{\text{G}}$ Gate, Nanowire Ferroelectric FET Memory Transistors. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 1637-1640	4-4	22
86	Nature of magnetic domains in an exchange coupled BiFeO <sub>3</sub> /CoFe heterostructure. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 112902	3-4	21
85	Analysis and Modeling of Inner Fringing Field Effect on Negative Capacitance FinFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 2023-2027	2-9	20
84	A Nitrided Interfacial Oxide for Interface State Improvement in Hafnium Zirconium Oxide-Based Ferroelectric Transistor Technology. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 95-98	4-4	20
83	Dependence of intrinsic performance of transition metal dichalcogenide transistors on materials and number of layers at the 5 nm channel-length limit <b>2013</b> ,		20
82	Hidden Magnetic States Emergent Under Electric Field, In A Room Temperature Composite Magnetoelectric Multiferroic. <i>Scientific Reports</i> , <b>2017</b> , 7, 15460	4-9	20
81	NCFET Design Considering Maximum Interface Electric Field. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 1254-1257	4-1	19

80	Response Speed of Negative Capacitance FinFETs <b>2018</b> ,		19
79	A Predictive Tunnel FET Compact Model With Atomistic Simulation Validation. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 599-605	2.9	18
78	Spacer Engineering in Negative Capacitance FinFETs. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1009-1012	4.4	18
77	Ultrafast magnetization switching in nanoscale magnetic dots. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 232407	3.4	18
76	Device design considerations for ultra-thin body non-hysteretic negative capacitance FETs <b>2013</b> ,		17
75	Quantitative model for TMR and spin-transfer torque in MTJ devices <b>2010</b> ,		17
74	Fully transparent field-effect transistor with high drain current and on-off ratio. <i>APL Materials</i> , <b>2020</b> , 8, 011110	5.7	16
73	Electrically induced, non-volatile, metal insulator transition in a ferroelectric-controlled MoS2 transistor. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 043107	3.4	16
72	Ballistic I-V Characteristics of Short-Channel Graphene Field-Effect Transistors: Analysis and Optimization for Analog and RF Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 958-964	2.9	16
71	Near Threshold Capacitance Matching in a Negative Capacitance FET With 1 nm Effective Oxide Thickness Gate Stack. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 179-182	4.4	16
70	BSIM Compact Model of Quantum Confinement in Advanced Nanosheet FETs. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 730-737	2.9	16
69	Ferroelectric Domain Wall Motion in Freestanding Single-Crystal Complex Oxide Thin Film. <i>Advanced Materials</i> , <b>2020</b> , 32, e1907036	2.4	16
68	Screening in Ultrashort (5 nm) Channel MoS2 Transistors: A Full-Band Quantum Transport Study. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 2457-2463	2.9	15
67	Variation Caused by Spatial Distribution of Dielectric and Ferroelectric Grains in a Negative Capacitance Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 4652-4658	2.9	15
66	. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1423-1426	4.4	14
65	Negative-Capacitance FinFET Inverter, Ring Oscillator, SRAM Cell, and Ft <b>2018</b> ,		14
64	One Nanometer HfO2-Based Ferroelectric Tunnel Junctions on Silicon. <i>Advanced Electronic Materials</i> , 2100499	6.4	14
63	Optimization of NCFET by Matching Dielectric and Ferroelectric Nonuniformly Along the Channel. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 822-825	4.4	13

62	Magnetic domain-wall motion twisted by nanoscale probe-induced spin transfer. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	13
61	Multidomain Phase-Field Modeling of Negative Capacitance Switching Transients. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 295-298	2.9	13
60	Ultrathin ferroic HfO-ZrO superlattice gate stack for advanced transistors.. <i>Nature</i> , <b>2022</b> , 604, 65-71	50.4	13
59	Epitaxial Ferroelectric Hf Zr O with Metallic Pyrochlore Oxide Electrodes. <i>Advanced Materials</i> , <b>2021</b> , 33, e2006089	24	12
58	Characterization and Modeling of Flicker Noise in FinFETs at Advanced Technology Node. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 985-988	4.4	11
57	Anomalous Beneficial Gate-Length Scaling Trend of Negative Capacitance Transistors. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1860-1863	4.4	11
56	Phenomenological Compact Model for QM Charge Centroid in Multigate FETs. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 1480-1484	2.9	11
55	Quantum Transport Simulation of Tunneling Based Spin Torque Transfer (STT) Devices: Design Trade offs and Torque Efficiency <b>2007</b> ,		11
54	Design Optimization Techniques in Nanosheet Transistor for RF Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 4515-4520	2.9	11
53	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 6752-6760	9.5	10
52	Low power negative capacitance FETs for future quantum-well body technology <b>2013</b> ,		10
51	Compact Modeling Source-to-Drain Tunneling in Sub-10-nm GAA FinFET With Industry Standard Model. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 3576-3581	2.9	10
50	Electric-field control of spin dynamics during magnetic phase transitions. <i>Science Advances</i> , <b>2020</b> , 6,	14.3	10
49	BSIM-HV: High-Voltage MOSFET Model Including Quasi-Saturation and Self-Heating Effect. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 4258-4263	2.9	9
48	Generation and stability of structurally imprinted target skyrmions in magnetic multilayers. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 112404	3.4	9
47	Emergent ferroelectricity in subnanometer binary oxide films on silicon.. <i>Science</i> , <b>2022</b> , 376, 648-652	33.3	9
46	Statistically meaningful measure of domain-wall roughness in magnetic thin films. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	8
45	Modeling of Advanced RF Bulk FinFETs. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 791-794	4.4	8

44	Self-Consistent Simulation of Hybrid Spintronic Devices <b>2006</b> ,		8
43	Unifying femtosecond and picosecond single-pulse magnetic switching in Gd-Fe-Co. <i>Physical Review B</i> , <b>2021</b> , 103,	3.3	8
42	Review of negative capacitance transistors <b>2016</b> ,		8
41	Negative-Capacitance FinFETs: Numerical Simulation, Compact Modeling and Circuit Evaluation <b>2018</b> ,		8
40	Modeling of Back-Gate Effects on Gate-Induced Drain Leakage and Gate Currents in UTB SOI MOSFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 3986-3990	2.9	7
39	Modeling SiGe FinFETs With Thin Fin and Current-Dependent Source/Drain Resistance. <i>IEEE Electron Device Letters</i> , <b>2015</b> , 36, 636-638	4.4	7
38	Phase field model of domain dynamics in micron scale, ultrathin ferroelectric films: Application for multiferroic bismuth ferrite. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 074102	2.5	7
37	Electrically controlled switching of the magnetization state in multiferroic BaTiO <sub>3</sub> /CoFe submicrometer structures. <i>Physical Review Materials</i> , <b>2018</b> , 2,	3.2	7
36	Surface states in a monolayer MoS <sub>2</sub> transistor. <i>Journal of Materials Research</i> , <b>2016</b> , 31, 911-916	2.5	7
35	Tunneling electroresistance effects in epitaxial complex oxides on silicon. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 032902	3.4	6
34	Possible route to low current, high speed, dynamic switching in a perpendicular anisotropy CoFeB-MgO junction using Spin Hall Effect of Ta <b>2012</b> ,		6
33	Compact Modeling of Temperature Effects in FDSOI and FinFET Devices Down to Cryogenic Temperatures. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 4223-4230	2.9	6
32	A Compact Model of Polycrystalline Ferroelectric Capacitor. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 5311-5314	2.9	6
31	Fast Read-After-Write and Depolarization Fields in High Endurance n-Type Ferroelectric FETs. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	6
30	One-Dimensional Spin Channel in Two-Dimensional Transition Metal Dichalcogenide Heterostructures. <i>IEEE Nanotechnology Magazine</i> , <b>2018</b> , 17, 1053-1057	2.6	5
29	Negative capacitance in ferroelectric materials and implications for steep transistors <b>2015</b> ,		5
28	<b>2017</b> ,		4
27	In situ ferromagnetic resonance capability on a polarized neutron reflectometry beamline. <i>Journal of Applied Crystallography</i> , <b>2018</b> , 51, 9-16	3.8	4



26	Micromagnetic analysis and optimization of spin-orbit torque switching processes in synthetic antiferromagnets. <i>Journal of Applied Physics</i> , <b>2019</b> , 126, 163905	2.5	4
25	Ferroelectric gate oxides for negative capacitance transistors. <i>MRS Bulletin</i> , <b>2021</b> , 46, 930	3.2	4
24	Electric Field-Induced Permittivity Enhancement in Negative-Capacitance FET. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 1346-1351	2.9	4
23	Novel Spin-Orbit Torque Generation at Room Temperature in an All-Oxide Epitaxial La Sr MnO /SrIrO System. <i>Advanced Materials</i> , <b>2021</b> , 33, e2008269	2.4	4
22	Memristors: A Spin-Orbit-Torque Memristive Device (Adv. Electron. Mater. 4/2019). <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1970022	6.4	3
21	Effect of anti-ferromagnet surface moment density on the hysteresis properties of exchange coupled antiferromagnet-ferromagnet systems: The case of bismuth-ferrite. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 103904	2.5	3
20	Dual-Source-Line-Bias Scheme to Improve the Read Margin and Sensing Accuracy of STTRAM in Sub-90-nm Nodes. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , <b>2010</b> , 57, 208-212	3.5	3
19	RKKY Exchange Bias Mediated Ultrafast All-Optical Switching of a Ferromagnet. <i>Advanced Functional Materials</i> , 2107490	15.6	3
18	<b>2020</b> ,		3
17	Analysis and Modeling of Polarization Gradient Effect on Negative Capacitance FET. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 4521-4525	2.9	3
16	Unified Framework for Charge-Spin Interconversion in Spin-Orbit Materials. <i>Physical Review Applied</i> , <b>2021</b> , 15,	4.3	3
15	Novel Cascadable Magnetic Majority Gates for Implementing Comprehensive Logic Functions. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 4687-4693	2.9	3
14	Logically synthesized and hardware-accelerated restricted Boltzmann machines for combinatorial optimization and integer factorization. <i>Nature Electronics</i> , <b>2022</b> , 5, 92-101	28.4	3
13	Intrinsic Limits to Contact Resistivity in Transition Metal Dichalcogenides. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1755-1758	4.4	2
12	Can piezoelectricity lead to negative capacitance? <b>2014</b> ,		2
11	A Compact Model of Metal/Ferroelectric-Insulator/Semiconductor Tunnel Junction. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 69, 414-418	2.9	2
10	Resonant Enhancement of Exchange Coupling for Voltage-Controlled Magnetic Switching. <i>Physical Review Applied</i> , <b>2020</b> , 14,	4.3	2
9	Ferroelectric Si-doped HfO <sub>2</sub> Capacitors for Next-Generation Memories <b>2019</b> ,		1

8	Mapping Polarity, Toroidal Order, and the Local Energy Landscape by 4D-STEM. <i>Microscopy and Microanalysis</i> , <b>2018</b> , 24, 176-177	0.5	1
7	A Compact Model of Antiferroelectric Capacitor. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	1
6	Large Injection Velocities in Highly Scaled, Fully Depleted Silicon on Insulator Transistors. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	0
5	Double-peaked resonance in harmonic-free acoustically driven ferromagnetic resonance. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 142403	3.4	0
4	Energy Storage and Reuse in Negative Capacitance. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 1861-1865	3.5	0
3	Atomic scale understanding of the electronic structure of 5d-3d perovskite oxide heterostructures using STEM-EELS.. <i>Microscopy and Microanalysis</i> , <b>2021</b> , 27, 356-358	0.5	
2	Magnetization Switching and Domain Wall Motion Due to Spin Orbit Torque <b>2016</b> , 165-187		
1	A Voltage-Controlled Gain Cell Magnetic Memory. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 1452-1455	4.4	